

Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	12	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} =4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	5.5 4.2	А
Continuous Drain Current (Note 6) V _{GS} =4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	6.6 5.3	А
Pulsed Drain Current (Note 7)			I _{DM}	30	Α

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	0.92	W
Total Power Dissipation (Note 6)	P _D	1.47	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	136	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	94	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

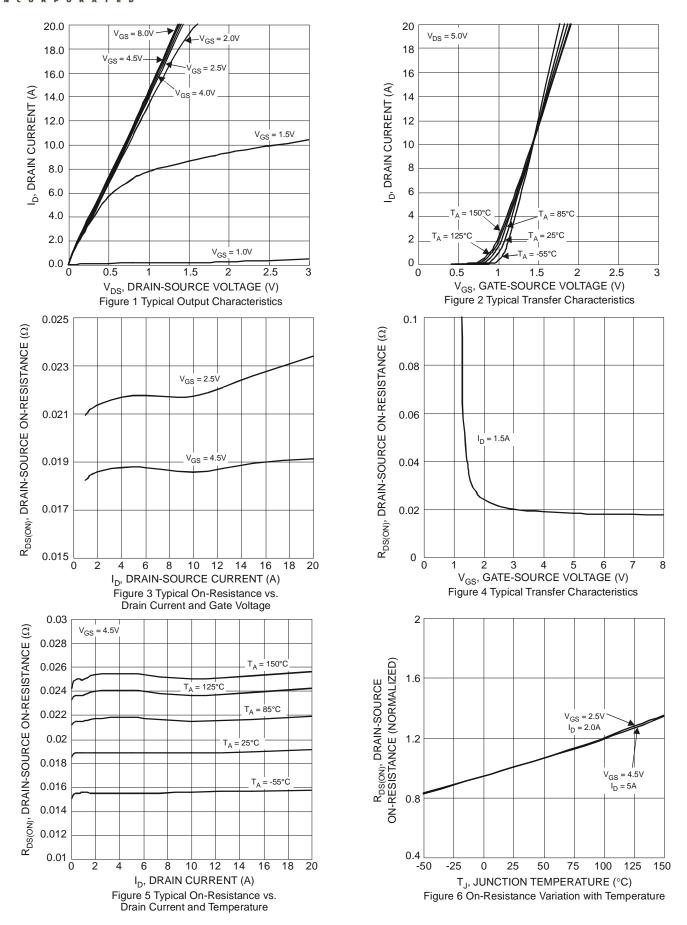
Characteristic		mbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	B\	V _{DSS}	12	_		V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current (@-	$\Gamma_{\rm C} = +25^{\circ}{\rm C}$	loss		_	1.0	μΑ	$V_{DS} = 9.6V, V_{GS} = 0V$	
Gate-Source Leakage	lo	lgss		_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	V _G	GS(TH)	0.4	0.6	1.0	>	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance			_	16	20	mΩ	$V_{GS} = 4.5V, I_D = 1.5A$	
Static Dialif-Source Off-Resistance	KD	OS(ON)	_	20	23	11112	$V_{GS} = 2.5V, I_D = 1.5A$	
Forward Transfer Admittance	Ŋ	Y _{FS}	_	14	_	S	$V_{DS} = 6V, I_{D} = 1.5A$	
Diode Forward Voltage (Note 6)	\	V _{SD}	_	0.7	1.0	>	V _{GS} = 0V, I _S = 1.5A	
Reverse Recovery Charge		Q _{RR}	_	8		nC	$V_{DD} = 6V, I_F = 1.5A,$	
Reverse Recovery Time	t	t _{RR}	_	43.6	_	ns	di/dt =200A/µs	
DYNAMIC CHARACTERISTICS (Note 9)	DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C	CISS	_	423	550	pF	V _{DS} = 6V, V _{GS} = 0V, -f = 1.0MHz	
Output Capacitance	С	Coss	_	238	310	pF		
Reverse Transfer Capacitance	С	CRSS	_	41	55	pF		
Series Gate Resistance	ı	R _G		3		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (4.5V)	(Q_G	_	4.2	5.5	nC	V _{GS} = 4.5V, V _{DS} = 6V, -I _D =1.5A	
Gate-Source Charge	C	Q _{GS}	_	0.6	_	nC		
Gate-Drain Charge	G	Q _{GD}	_	0.4	_	nC		
Turn-On Delay Time	t _D	D(ON)	_	5	8	ns		
Turn-On Rise Time		t _R	_	10	_	ns	$V_{DS} = 6V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(}	O(OFF)	_	25	40	ns	$R_G = 4\Omega$, $I_D = 1.5A$	
Turn-Off Fall Time		t _F	_	10		ns		

Notes:

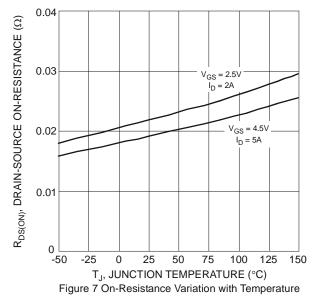
- 5. Device mounted on FR-4 PCB with minimum recommended pad layout.
 6. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz (0.071-mm thick) Cu.
- 7. 300ms pulse, pulse duty cycle<=2%.

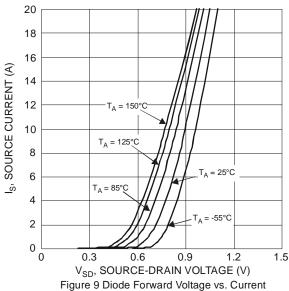
 8. Short duration pulse test used to minimize self-heating effect.
- Guaranteed by design. Not subject to production testing.

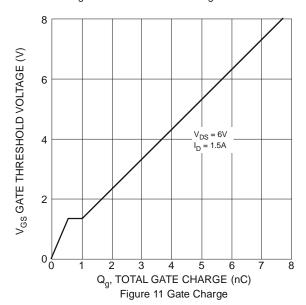












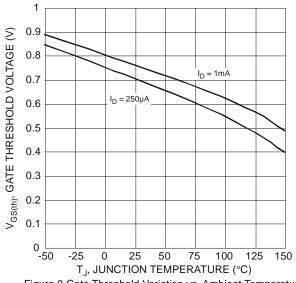
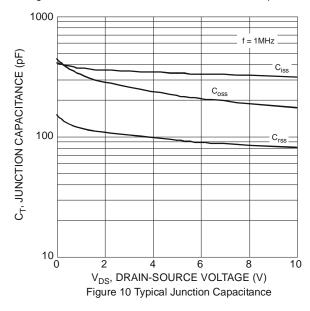


Figure 8 Gate Threshold Variation vs. Ambient Temperature



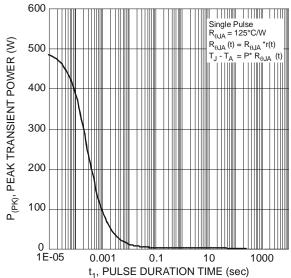
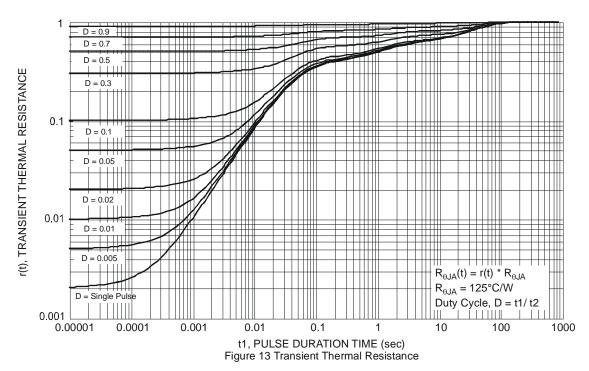


Figure 12 Single Pulse Maximum Power Dissipation



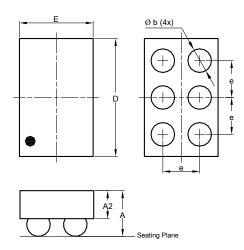




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-WLB1510-6

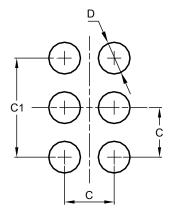


U-WLB1510-6						
Dim	Min	Max	Тур			
Α	_	0.62	_			
A2		_	0.038			
b	0.27	0.37	0.32			
D	1.40	1.50	1.50			
Е	0.90	1.00	1.00			
е	_	_	0.50			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-WLB1510-6



Dimensions	Value (in mm)		
С	0.50		
C1	1.00		
D	0.25		



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